

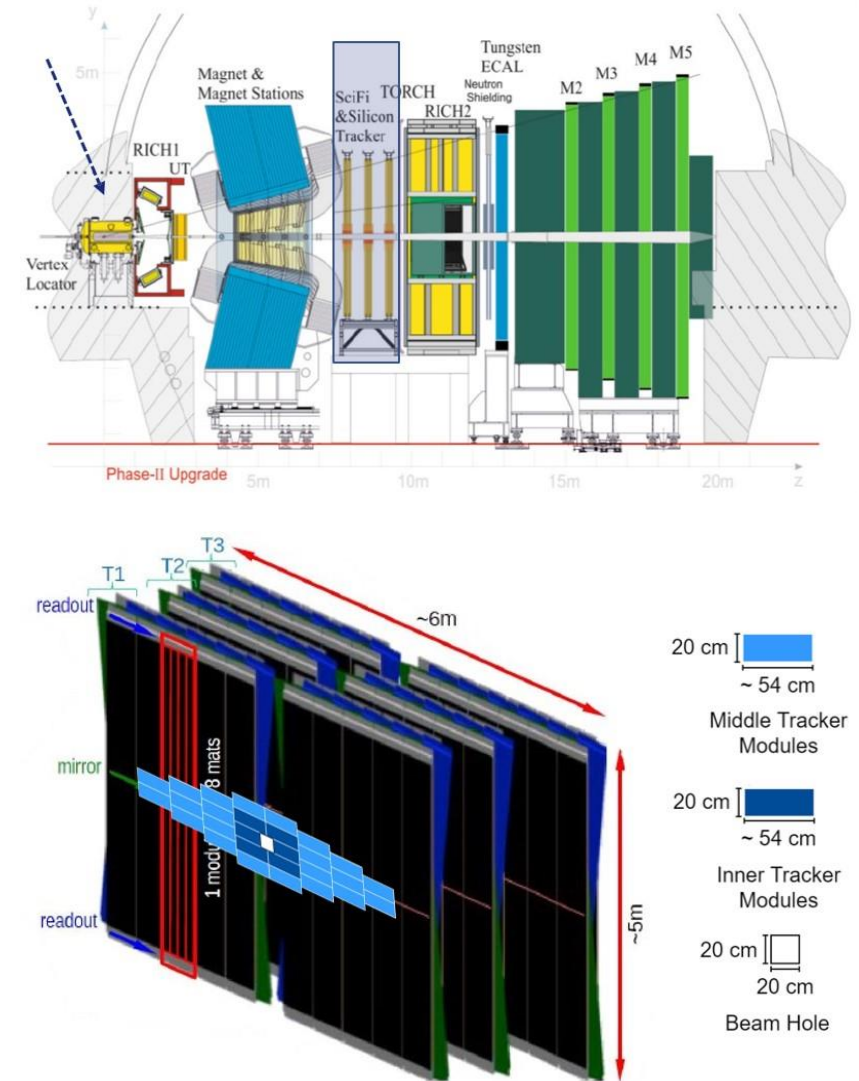
CMOS sensor for the LHCb Mighty Tracker and RD50

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The Mighty Tracker at LHCb

- Upgrades of the detector systems are required to cope with the increased luminosity anticipated in the coming runs
- Proposed hybrid tracker composed of
 - Scintillating Fibre Tracker (SciFi)**
 - Scintillating fibres with SiPM readout
 - Installed in LS2, replacements in LS3
 - Inner Tracker (IT) and Middle Tracker (MT)**
 - Monolithic High Voltage-CMOS sensors**
 - To meet the anticipated requirements on granularity, radiation tolerance and cost
 - Installation planned for LS3 and LS4

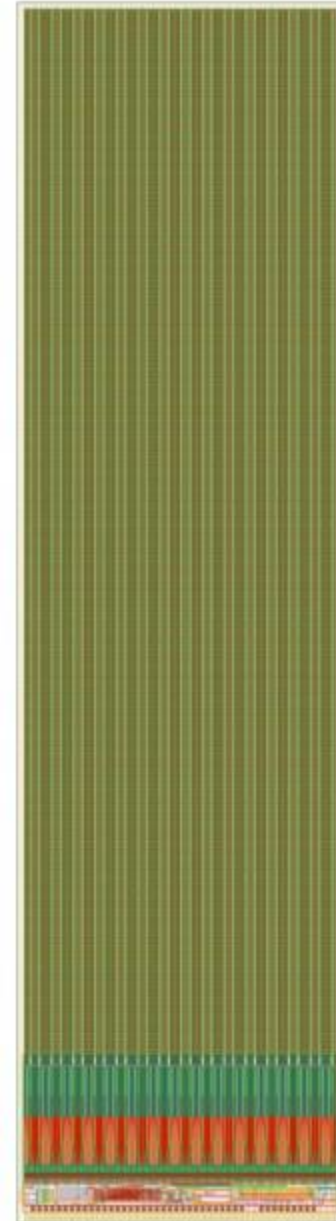


MightyPix R&D programme

- Dedicated R&D programme to develop a High Voltage-CMOS sensor chip that meets the Mighty Tracker requirements
 - **Pixel size** → $< 100 \mu\text{m} \times 300 \mu\text{m}$
 - **Timing resolution** → $\sim 3\text{ns}$
 - **In-time efficiency** → $> 99\%$
 - **Radiation tolerance** → $6\text{E}14 \text{ n}_{\text{eq}}/\text{cm}^2$
 - **Power consumption** → $< 150 \text{ mW}/\text{cm}^2$
 - **Compatibility with the LHCb readout system**
- The programme foresees several High Voltage-CMOS sensor chip submissions
 - **MightyPix1 (2022)** → first prototype dedicated to the Mighty Tracker
 - **MightyPix2 (2023)** → full LHCb engineering run submission (2 cm x 2 cm) & 100% compatibility with LHCb readout system
 - **MightyPix3 (2024)** → production sensor chip for LS3
 - **MightyPix4 (2027-28)** → improved sensor chip for LS4

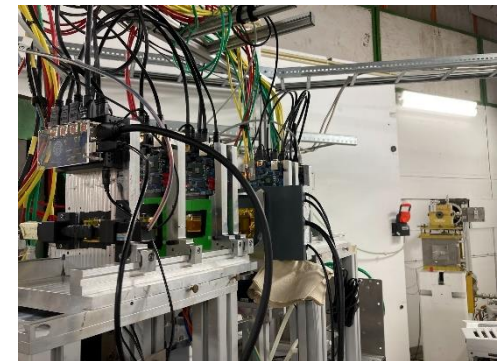
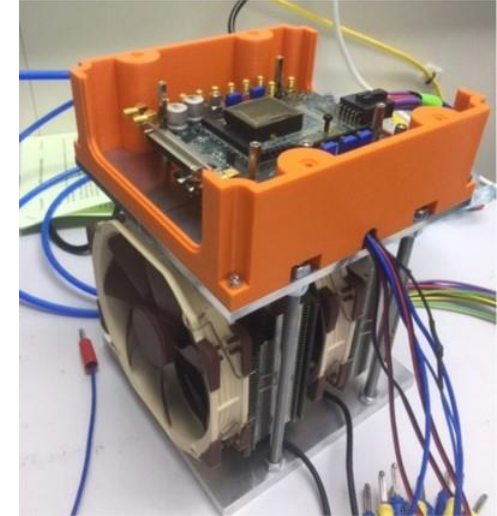
MightyPix1

- **First High Voltage-CMOS sensor dedicated to the Mighty Tracker**
 - Pixel size: 55 μm x 165 μm
 - 320 rows, 29 columns
 - Chip size: 0.5 x \sim 2 cm
 - $\frac{1}{4}$ of final MightyPix size \rightarrow $\frac{1}{4}$ width, full column length
 - First prototype compatible with LHCb readout system
 - Runs with LHC clock at 40 MHz
 - Uses IpGBT protocol
 - Meets TFC and ECS requirements
 - Designed by KIT with some inputs from Uni. Liverpool
 - Submitted in May 2022 for fabrication with TSI (180 nm node)
 - Delivery expected in December 2022



Ongoing evaluation programme

- **Use existing, similar prototypes to evaluate key parameters such as timing performance after irradiation to relevant fluence in both the lab and test beams**
 - Chip used: ATLASPix3.1
 - Full size High Voltage CMOS demonstrator for ATLAS ITk in TSI 180 nm
 - Pixel size: 50 μm x 150 μm
 - Similar analogue front-end architecture as MightyPix
 - Irradiated up to $3\text{E}15$ $n_{\text{eq}}/\text{cm}^2$
 - Evaluated at DESY test beam at three operating temperatures: -10, 0 and +5 $^{\circ}\text{C}$
 - Analysis ongoing, but results are promising (LHCb note to be published soon)
- **Motivation is to inform the MightyPix mechanics design effort of the best operating temperature to develop a cooling strategy**



CMOS and monolithic devices



RD50-MPW1

DAQ (Caribou)

$I_{LEAK} \uparrow, V_{BD} \downarrow$

RD50-MPW4



TCAD

eTCT

RD50-MPW2

Irradiation studies

Improved performance

Timing studies

Wafer 13, $1e14 N_{eq}$

RD50-MPW3

Delivered in 07.2022

64 × 64 pixel matrix

digital readout periphery

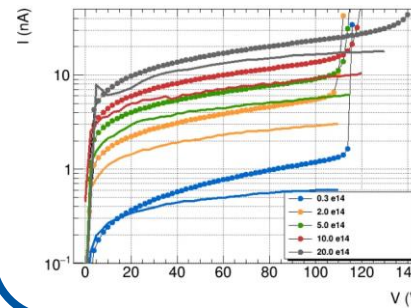
CMOS and monolithic devices



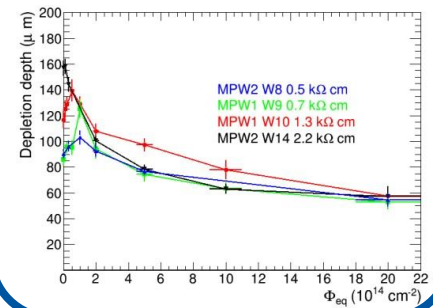
RD50-MPW2: Prototype HV-CMOS sensor with test structures and a small active pixel matrix, fabricated in high resistivity substrates in a Multi-Project Wafer submission with LFoundry.

- Aim to study and improve time resolution and radiation tolerance with high granularity pixels (60 μm x 60 μm)
- Evaluated in the lab before and after neutron irradiation up to $2\text{E}15 \text{ n}_{\text{eq}}/\text{cm}^2$

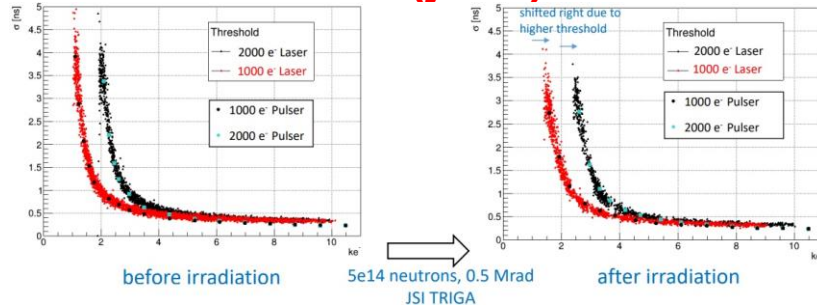
I-V (after 80 mins annealing)



eTCT @ $V_{\text{HV}} = 100 \text{ V}$, $2 \text{ k}\Omega\text{cm}$

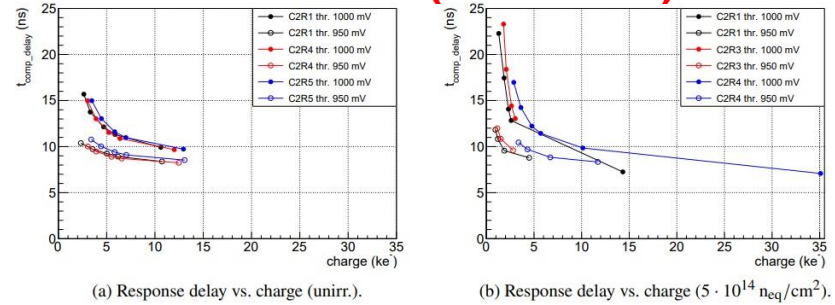


Time resolution (jitter)



Jitter < 160 ps before and after irradiation to $5\text{E}14$

Time resolution (time-walk)



Time-walk < 10 ns before and after irradiation to $5\text{E}14$ @ $> 2\text{ke}^-$ collected

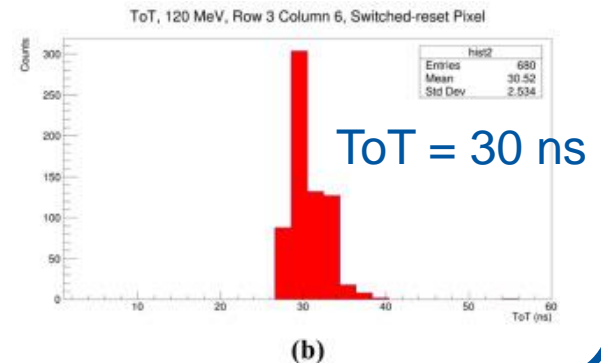
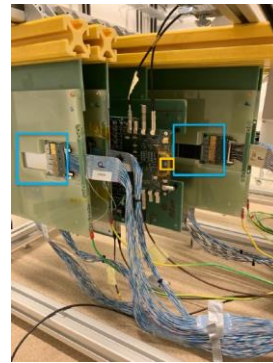
CMOS and monolithic devices



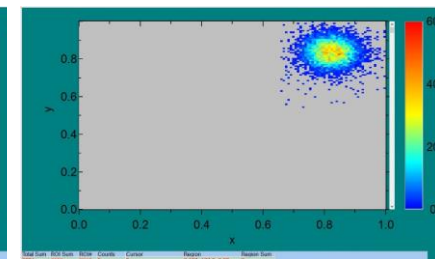
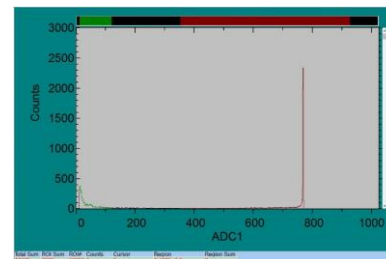
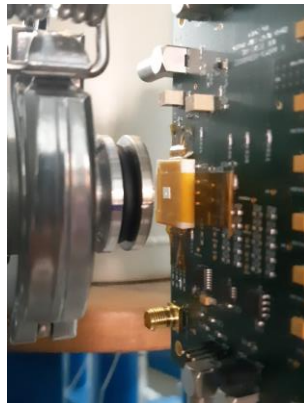
RD50-MPW2: Prototype HV-CMOS sensor with test structures and a small active pixel matrix, fabricated in high resistivity substrates in a Multi-Project Wafer submission with LFoundry.

- Evaluated at proton (medical) and ion beam facilities
- To validate the DAQ and obtain first results

Proton test beam



Ion test beam



2 MeV proton microbeam

Results suggest the presence of SETs, further studying with simulation tools

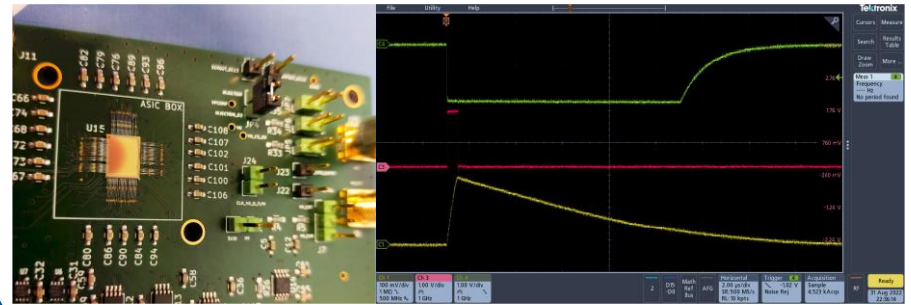
CMOS and monolithic devices



RD50-MPW3: Prototype HV-CMOS sensor with advanced test structures and a 64 x 64 active pixel matrix, fabricated in high resistivity substrates in a Multi-Project Wafer submission with LFoundry.

- Improved design to enable a wider range of measurements
- Beam time booked at SPS (10.2022, non-irradiated samples); test beam with irradiated samples planned
- Neutron and proton irradiation campaigns ongoing

**Initial lab evaluation is satisfactory
(samples delivered in 07.2022)**



Improvements include:

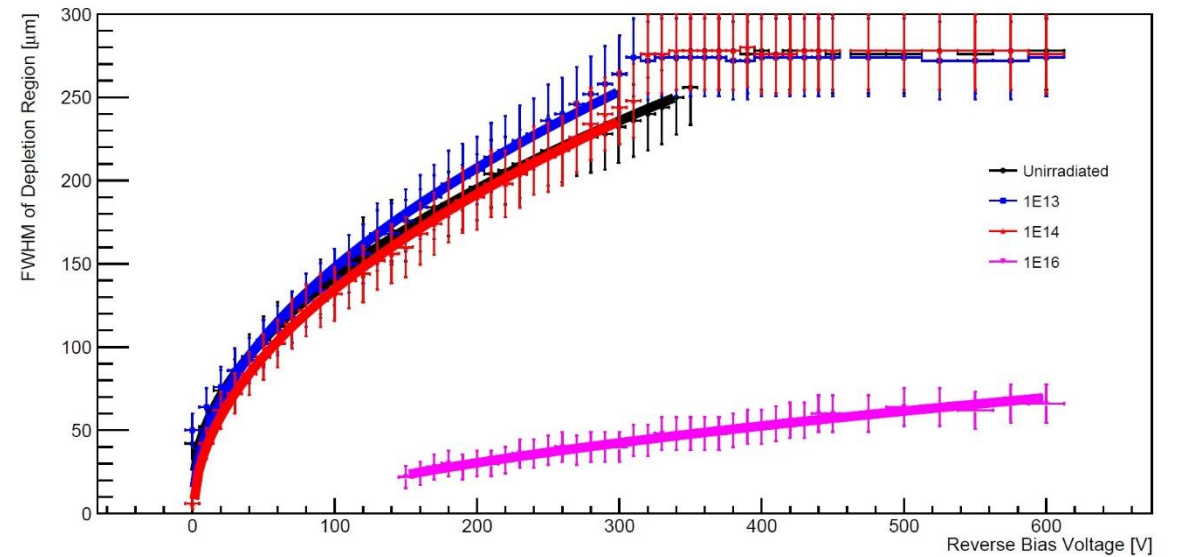
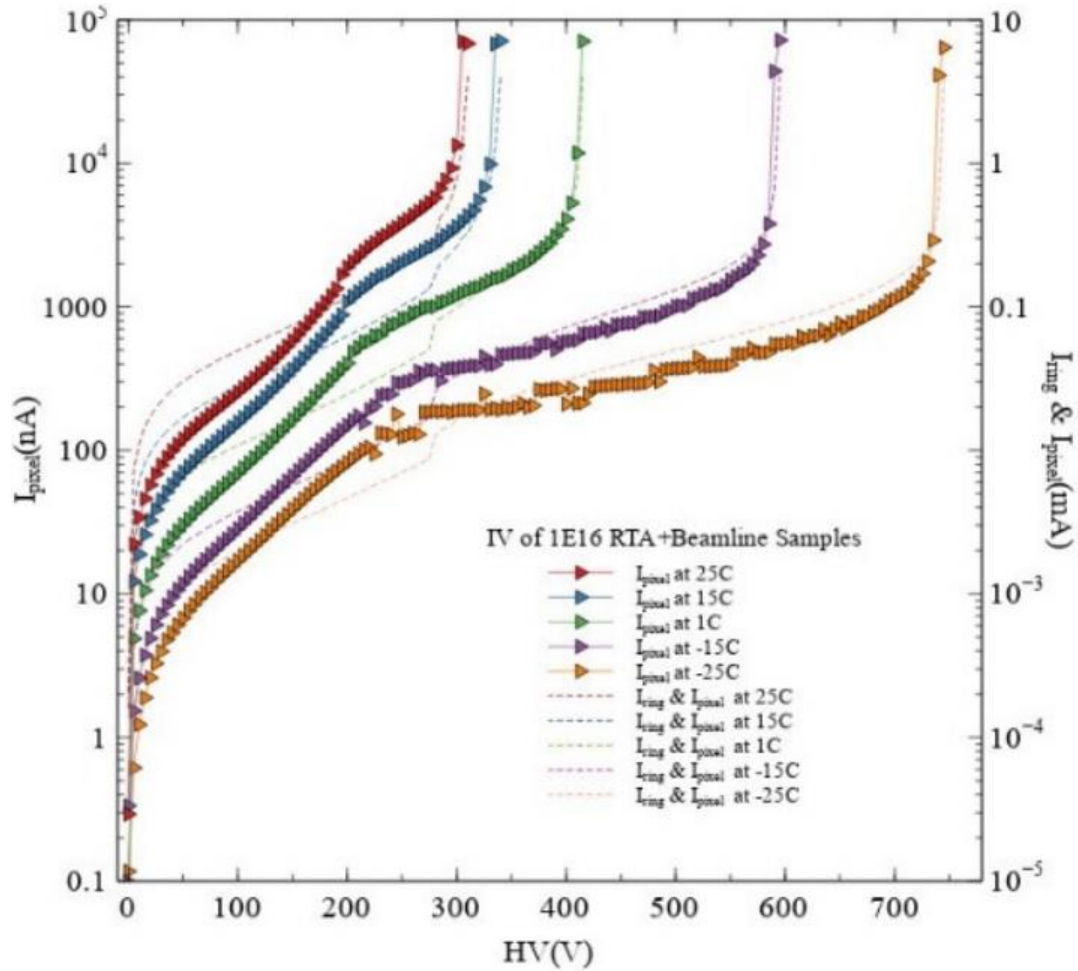
- Larger number of active pixels in matrix (64 x 64 pixels)
- Analogue and digital readout embedded in small pixel area (62 μm x 62 μm)
- Optimised design to minimise crosstalk noise, to speed sensor configuration and to speed data readout
- Advanced test structures with guard rings to further improve I-V and also to evaluate defect concentration before and after irradiation

Future work



- Continue activities to further study and develop the sensor with low-cost submissions
- Evaluate RD50-MPW3 in the lab and in test beams before and after proton and neutron irradiation to high fluence
- Design and submit a new and larger prototype (RD50-MPW4) with all the lessons learned so far
- Optimise the design with backside biasing for operation beyond $E16 n_{eq}/cm^2$
- Evaluate RD50-MPW4

Generic R&D at Uni. Liverpool



Preliminary